PATENT ABSTRACTS OF JAPAN

(11)Publication number:

2001-152339

(43)Date of publication of application: 05.06.2001

(51)Int.CL

C23C 16/40 C23C 16/34 C23C 16/44 H01L 21/316

H01L 21/318

(21)Application number: 2000-307849

(71)Applicant: SAMSUNG ELECTRONICS CO LTD

(22)Date of filing:

06.10.2000

(72)Inventor: KIN EIKAN

PARK YOUNG-WOOK LIM JAE-SOON **CHOI SUNG-JE**

LEE SANG-IN

(30)Priority

Priority number: 1999 9943056

Priority date: 06.10.1999

Priority country: KR

1999 9950902 2000 200014824

16.11.1999 23.03.2000 KR **KR**

2000 200053415

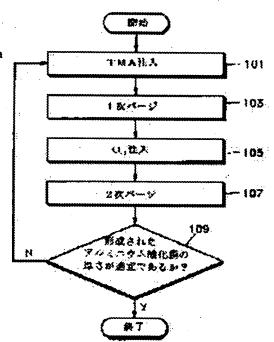
08.09.2000

KR

(54) THIN FILM DEPOSITION METHOD USING AN ATOMIC LAYER VAPOR DEPOSITION METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a thin film deposition method using an atomic layer vapor deposition method. SOLUTION: A first reactant containing an element to deposit a thin film and a ligand is poured into a reaction chamber containing a substrate and is purged, and next, a second reactant is poured and purged. Using a substance having bond energy with the element to deposit a thin film higher than that of the ligand, by the chemical reaction between the element to form into a thin film and the secondary reactant, a thin film is deposited, and moreover, the production of side-reactants is prevented. Alternatively, as the second reactant, a substance which does not contain a hydroxyl group is used, and after the purge of the second reactant, the same is again brought into reaction with a third reactant containing a hydroxyl group, by which the production of by-products of the hydroxyl group in the thin film is prevented. Alternatively, after the purge of the second reactant, for removing impurities and improving stoichiometry, the third reactant is poured ad purged. In this way, the thin film which does not contain impurities and is also excellent in stoichiometry can be obtained.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]